CLAIMS

1. An arrangement of several resistors comprising: the resistors jointly positioned in one and the same well of a semiconductor device, wherein the resistors, when viewed in a longitudinal direction of the resistors, are displaced in relation to one another.

2. The arrangement according to claim 1, wherein the resistors all have substantially the same length.

3. The arrangement according to claim 1, wherein the resistors all have substantially the same breadth or width, respectively.

4. The arrangement according to claim 1, wherein the resistors all have substantially the same depth.

5. The arrangement according to claim 1, wherein the resistors all are of substantially identical structure.

6. The arrangement according to claim 1, wherein the resistors all have substantially the same individual resistance value.

7. The arrangement according to claim 1, said arrangement comprising more than two or three resistors.

8. The arrangement according to claim 1, said arrangement comprising more than four or five resistors.

9. The arrangement according to claim 1, wherein the resistors, when viewed in a longitudinal direction of the resistors, are displaced alternately to a front end and to a rear end.

10. The arrangement according to claim 1, wherein a first resistor of said resistors is displaced approximately a length of a second resistor of said resistors, wherein said first resistor is adjacent to said second resistor.

11. The arrangement according to claim 1, wherein a distance between a first resistor of said resistors and a second resistor of said resistors, when viewed in a transverse direction of the resistors, is smaller than one third of a breadth or width, and/or smaller than one third of a length of said first resistor or of said second resistor, respectively.

12. The arrangement according to claim 1, wherein a distance between a first resistor of said resistors and a second resistor of said resistors, when viewed in a transverse direction of the resistors, is smaller than either one fifth or one tenth of a breadth or width, and/or smaller than either one fifth or one tenth of a length of said first resistor or of said second resistor, respectively.

13. The arrangement according to claim 1, wherein the well is relatively weakly doped, in particular relatively weakly n-doped.

14. The arrangement according to claim 1, wherein the resistors are relatively strongly doped, in particular relatively strongly n-doped.

15. The arrangement according to claim 14, wherein the resistors are n-diffusion resistors.

16. The arrangement according to claim 1, wherein the resistors are connected to corresponding signal driver devices of the semiconductor device.

17. The arrangement according to claim 1, wherein the resistors are connected to corresponding output pads of the semiconductor device.

18. The arrangement according to claim 1, wherein the resistors are connected in parallel.

19. The arrangement according to claim 18, wherein the resistors are connected in parallel such that a total resistance value results for the resistors connected in parallel which corresponds to a desired resistance value.

20. The arrangement according to claim 19, wherein the resistors connected in parallel are jointly connected to a particular signal driver device, and wherein the desired resistance value corresponds to a resistance value desired for the corresponding signal driver device.

21. A semiconductor device comprising: an arrangement of resistors, the arrangement includes the resistors jointly positioned in one and the same well of a semiconductor device, wherein the resistors, when viewed in a longitudinal direction of the resistors, are displaced in relation to one another.